

Power MOSFET

PRODUCT SUMMARY

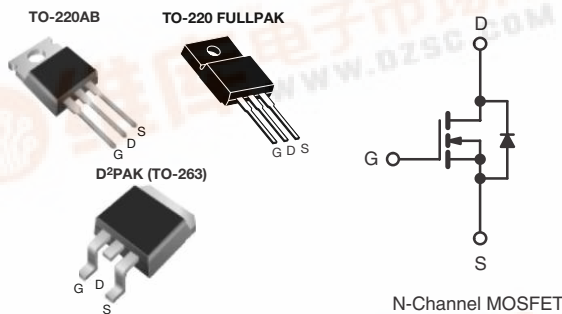
V_{DS} (V) at T_J max.	560 V	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10$ V	0.38
Q_g (Max.) (nC)	68	
Q_{gs} (nC)	17.6	
Q_{gd} (nC)	21.8	
Configuration	Single	

FEATURES

- Low Figure-of-Merit $R_{on} \times Q_g$
- 100 % Avalanche Tested
- Gate Charge Improved
- T_{rr}/Q_{rr} Improved
- Compliant to RoHS Directive 2002/95/EC



Available
RoHS*
COMPLIANT



ORDERING INFORMATION

Package	TO-220AB	D ² PAK (TO-263)	TO-220 FULLPAK
Lead (Pb)-free	SiHP16N50C-E3	SiHB16N50C-E3	SiHF16N50C-E3

ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ\text{C}$, unless otherwise noted

PARAMETER				SYMBOL	LIMIT		UNIT
					TO220-AB D ² PAK (TO-263)	TO-220 FULLPAK	
Drain-Source Voltage				V _{DS}	500		V
Gate-Source Voltage				V _{GS}	± 30		
Continuous Drain Current (T _J = 150 °C) ^a	V _{GS} at 10 V	T _C = 25 °C		I _D	16		A
		T _C = 100 °C			10		
Pulsed Drain Current ^c				I _{DM}	40		
Linear Derating Factor					2		W/°C
Single Pulse Avalanche Energy ^b				E _{AS}	320		mJ
Maximum Power Dissipation				P _D	250	38	W
Operating Junction and Storage Temperature Range				T _J , T _{stg}	- 55 to + 150		°C
Soldering Recommendations (Peak Temperature) ^d		for 10 s		300			

Notes

- Limited by maximum junction temperature.
- $V_{DD} = 50$ V, starting $T_J = 25^\circ\text{C}$, $L = 2.5$ mH, $R_g = 25\ \Omega$, $I_{AS} = 16$ A.
- Repetitive rating; pulse width limited by maximum junction temperature.
- 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

SiHP16N50C, SiHB16N50C, SiHF16N50C



Vishay Siliconix, SiHB16N50C, SiHF16N50C"供应商

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TO220-AB D ² PAK (TO-263)	TO-220 FULLPAK	UNIT
Maximum Junction-to-Ambient	R_{thJA}	62	65	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	0.5	3.3	
Junction-to-Ambient (PCB mount) ^a	R_{thJA}	40	-	

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	500	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25°C , $I_D = 1\text{ mA}$	-	0.6	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	3.0	-	5.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30\text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 500\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	50	μA
		$V_{DS} = 400\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125^\circ\text{C}$	-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 8\text{ A}$	-	0.31	0.38	Ω
Forward Transconductance ^a	g_{fs}	$V_{DS} = 50\text{ V}$, $I_D = 3\text{ A}$	-	3	-	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1.0\text{ MHz}$	-	1900	-	pF
Output Capacitance	C_{oss}		-	230	-	
Reverse Transfer Capacitance	C_{rss}		-	24	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$, $I_D = 16\text{ A}$, $V_{DS} = 400\text{ V}$	-	45	68	nC
Gate-Source Charge	Q_{gs}		-	18	-	
Gate-Drain Charge	Q_{gd}		-	22	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 250\text{ V}$, $I_D = 16\text{ A}$, $R_g = 9.1\text{ }\Omega$, $V_{GS} = 10\text{ V}$	-	27	-	ns
Rise Time	t_r		-	156	-	
Turn-Off Delay Time	$t_{d(off)}$		-	29	-	
Fall Time	t_f		-	31	-	
Gate Input Resistance	R_g	$f = 1\text{ MHz}$, open drain	-	1.6	-	Ω
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	16	A
Pulsed Diode Forward Current	I_{SM}		-	-	30	
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}$, $I_S = 10\text{ A}$, $V_{GS} = 0\text{ V}$	-	-	1.8	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25^\circ\text{C}$, $I_F = I_S$, $dI/dt = 100\text{ A}/\mu\text{s}$, $V_R = 20\text{ V}$	-	555	-	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	5.5	-	μC
Body Diode Reverse Recovery Current	I_{RRM}		-	18	-	A

Note

- The information shown here is a preliminary product proposal, not a commercial product data sheet. Vishay Siliconix is not committed to produce this or any similar product. This information should not be used for design purposes, nor construed as an offer to furnish or sell such products.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

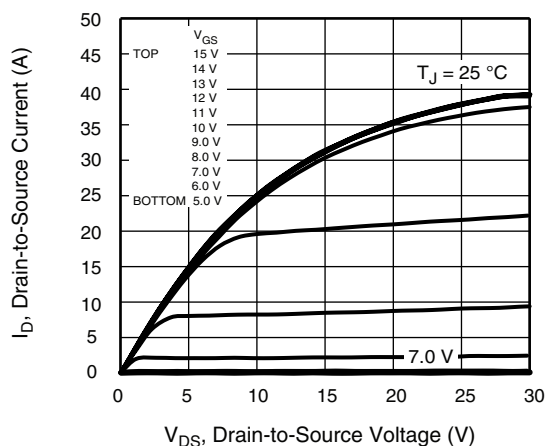


Fig. 1 - Typical Output Characteristics (TO-220)

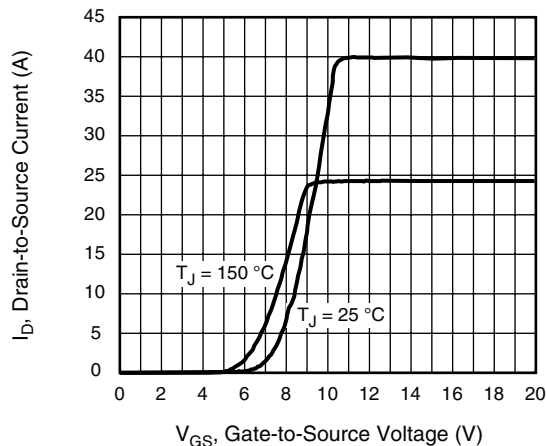


Fig. 3 - Typical Transfer Characteristics

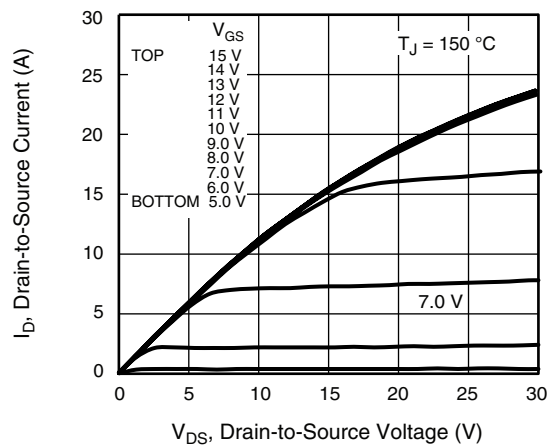


Fig. 2 - Typical Output Characteristics (TO-220)

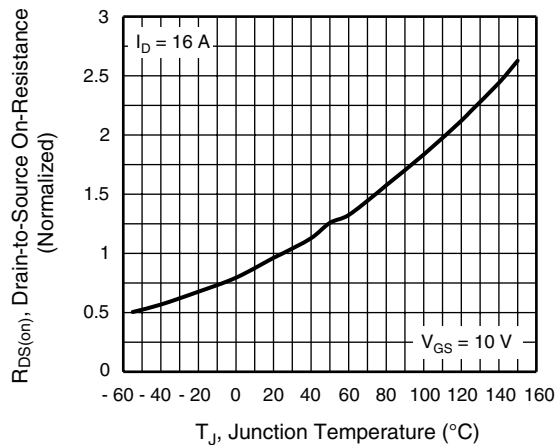


Fig. 4 - Normalized On-Resistance vs. Temperature

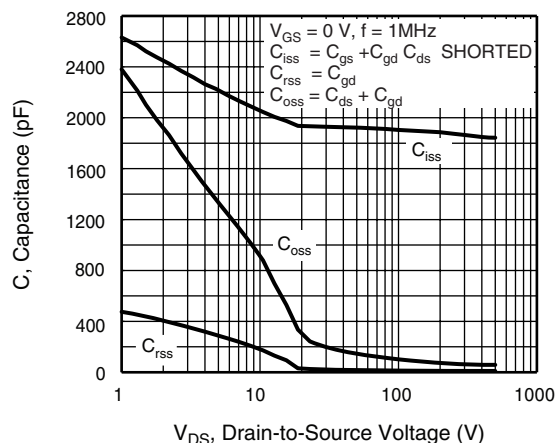


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

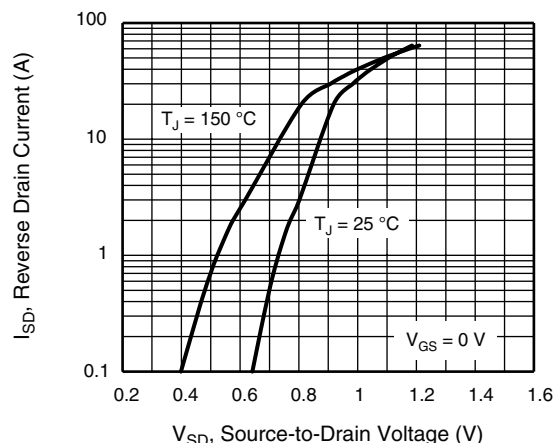


Fig. 7 - Typical Source-Drain Diode Forward Voltage

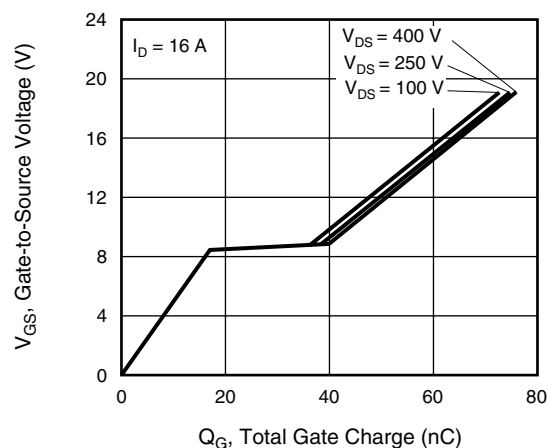


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

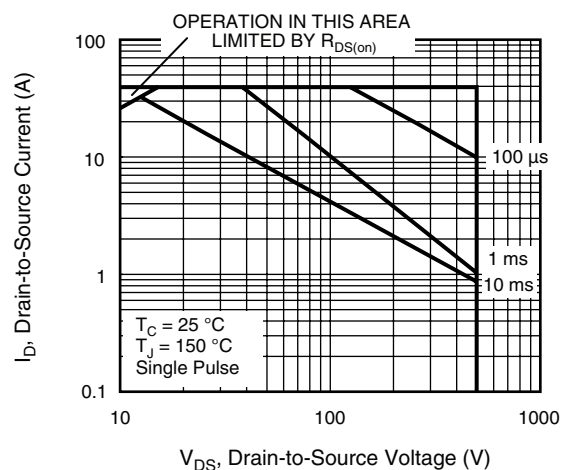


Fig. 8 - Maximum Safe Operating Area (TO-220AB, D²PAK)

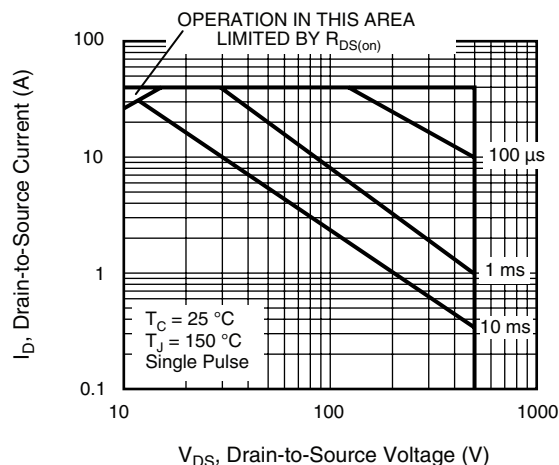


Fig. 9 - Maximum Safe Operating Area (TO-220 FULLPAK)

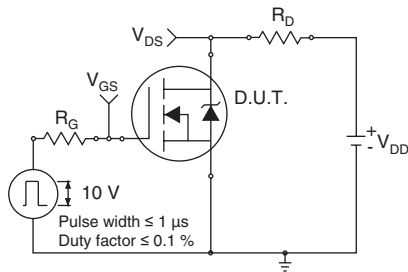


Fig. 10a - Switching Time Test Circuit

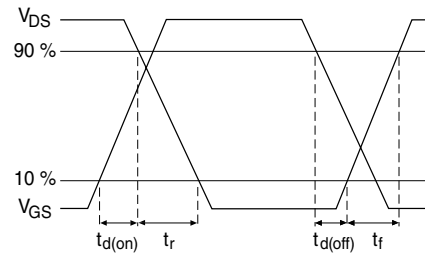


Fig. 10b - Switching Time Waveforms

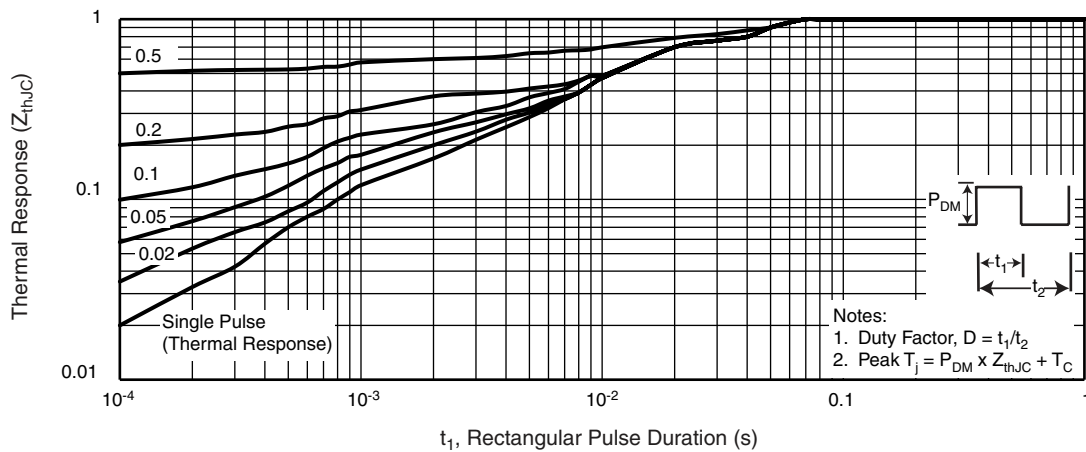


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case (TO-220AB, D²PAK)

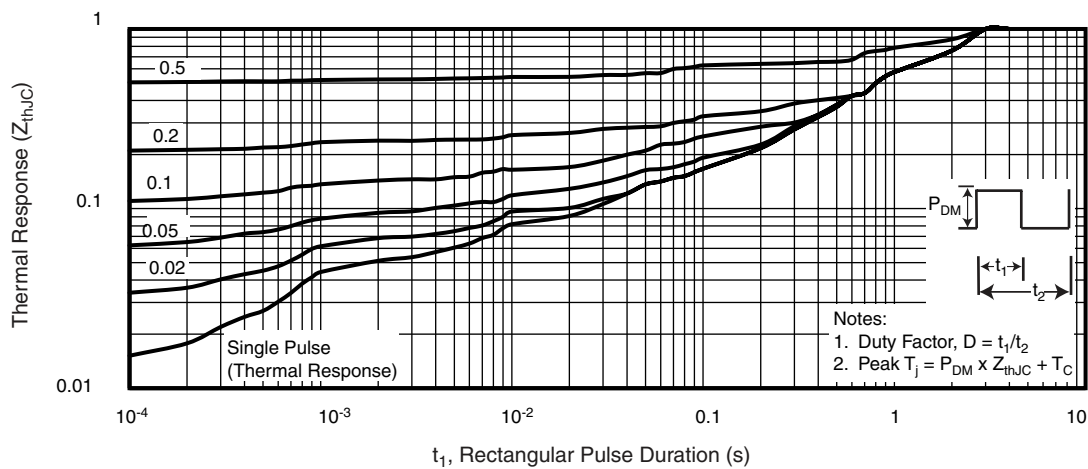


Fig. 12 - Maximum Effective Transient Thermal Impedance, Junction-to-Case (TO-220 FULLPAK)

SiHP16N50C, SiHB16N50C, SiHF16N50C



[Vishay Siliconix, SiHB16N50C, SiHF16N50C"供应商](#)

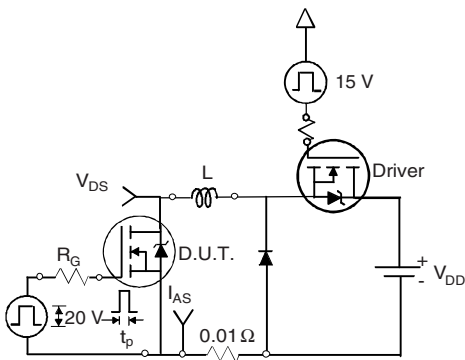


Fig. 13a - Unclamped Inductive Test Circuit

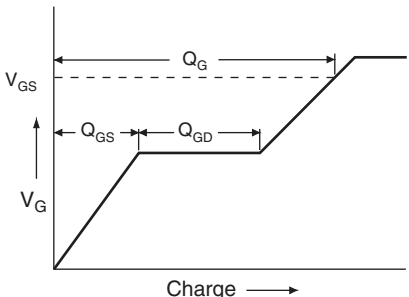


Fig. 14a - Basic Gate Charge Waveform

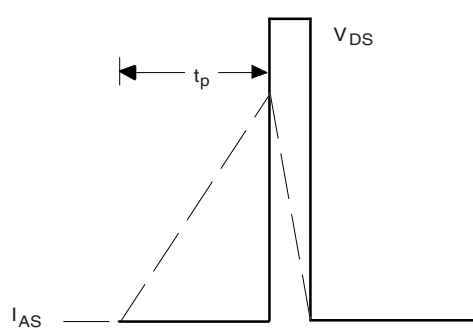


Fig. 13b - Unclamped Inductive Waveforms

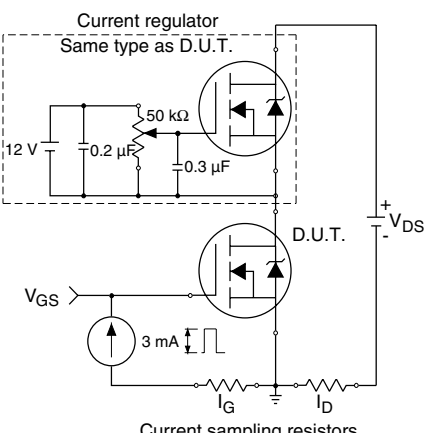
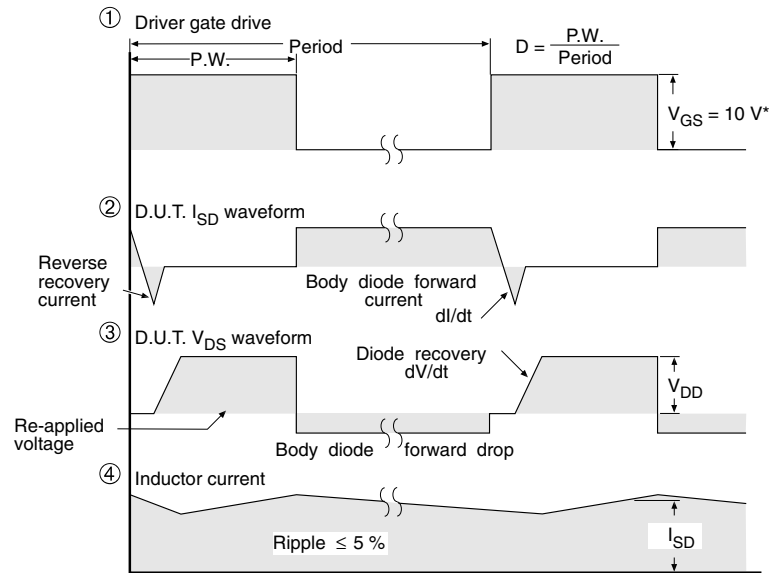
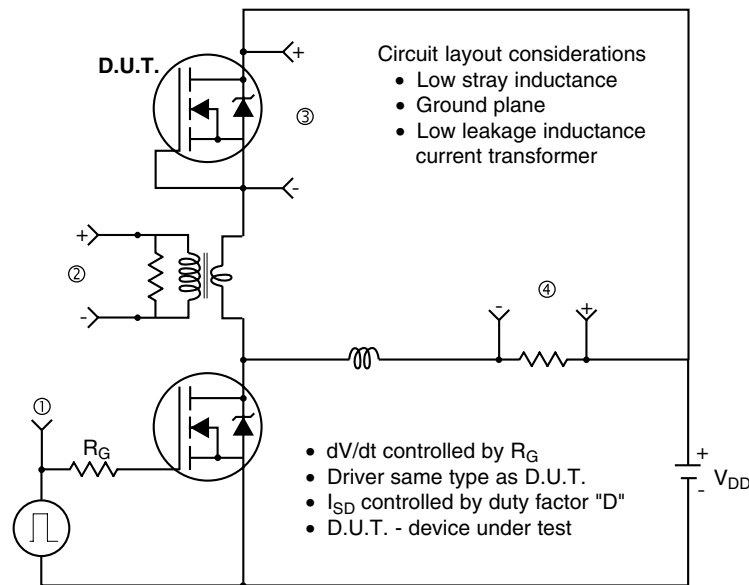


Fig. 14b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



* $V_{GS} = 5 V$ for logic level devices

Fig. 15 - For N-Channel

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